



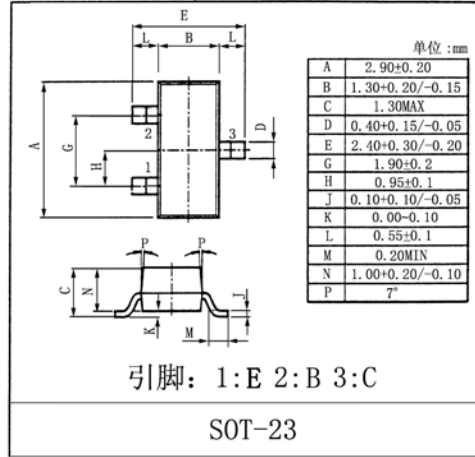
2SA1015M (3CG1015M)

硅 PNP 半导体三极管/SILICON PNP TRANSISTOR

用途:用于普通音频放大, 激励级放大/Purpose: Audio frequency general purpose amplifier applications, driver stage amplifier applications.

极限参数/Absolute maximum ratings(Ta=25°C)

参数符号 Symbol	数值 Rating	单位 Unit
V _{CB0}	-50	V
V _{CE0}	-50	V
V _{EB0}	-5.0	V
I _C	-150	mA
I _B	-50	mA
P _C	300	mW
T _j	150	°C
T _{stg}	-55~150	°C



电性能参数/Electrical characteristics(Ta=25°C)

参数符号 Symbol	测试条件 Test condition	数值 Rating			单位 Unit
		最小值 Min	典型值 Typ	最大值 Max	
I _{CB0}	V _{CB} =-50V I _E =0			-0.1	μA
I _{EB0}	V _{EB} =-5.0V I _C =0			-0.1	μA
h _{FE(1)}	V _{CE} =-6.0V I _C =-2.0mA	70		400	
h _{FE(2)}	V _{CE} =-6.0V I _C =-150mA	25			
V _{CE(sat)}	I _C =-100mA I _B =-10mA		-0.1	-0.3	V
V _{BE(sat)}	I _C =-100mA I _B =-10mA			-1.1	V
f _T	V _{CE} =-10V I _C =-1.0mA	80			MHz
C _{ob}	V _{CB} =-10V I _E =0 f=1.0MHz		4.0	7.0	pF
r _{bb'}	V _{CB} =-10V I _E =1.0mA f=30MHz		30		Ω
NF	V _{CE} =-6.0V I _C =-0.1mA R _g =10KΩ f=1.0KHz		1.0	10	dB

h_{FE(1)}分档/h_{FE(1)} Classifications:

h _{FE(1)} 分档 h _{FE(1)} Classifications	0	Y	GR
h _{FE(1)} 范围 h _{FE(1)} Range	70~140	120~240	200~400
印章 Marking	HBAO	HBAY	HBAG



2SA1015M (3CG1015M)

